Unusual Locking of Silicon Chains into *all-transoid* Conformation by Pentacoordinate Silicon Atoms

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Conformation of flexible linear chains are of fundamental importance in determining the physical properties of organic and inorganic polymers.¹ Over the past decade, a great deal of effort has been made for conformational control of silicon chains² because electronic and optical properties of σ -conjugated silicon polymers such as polysilanes and polycarbosilanes are highly sensitive to subtle changes in the backbone conformation.³ In this regard, conformational locking of the silicon chains into an alltransoid form is essential for realizing the useful physical properties of silicon compounds,⁴ since all-transoid conformation allows effective σ -conjugation along the silicon chain.^{2g,3b} However, conformational control of a silicon chain is extremely difficult, since the rotational barriers about Si-Si single bonds are so small that essentially free rotation occurs at room temperature. For example, the energy barrier to the rotation about the Si2-Si3 bond of Si₄Me₁₀ is predicted to be only 3.5 kcal/ mol, which is significantly smaller than that of the corresponding C3-C4 bond of octamethylhexane (>20 kcal/mol), revealing the greater flexibility of silicon chains compared with carbon chains.⁵

We report herein unusual locking of silicon chains into *all-transoid* conformation by pentacoordinate silicon atoms. Thus, the internal rotation about the Si–Si single bonds of pentacoordinate pentasilane **1** was found to be nearly completely inhibited even in a room-temperature solution, although there are no significant steric interactions between the substituents (Figure 1).

Pentacoordinate pentasilane **1** was prepared by the reaction of *N*-methyl-*N*-trimethylsilylacetamide with {Me₃SiSi(CH₂Cl)-Cl}₂SiMe₂ (1:1 mixture of diastereomers) in hexane at room temperature.⁶ The reaction stereoselectively gave the *dl*-isomer of **1**, which was recrystallized from hexane/benzene to give analytically pure **1** in 81% yield as colorless, benzene-containing crystals.

X-ray analysis of **1** revealed that strong intramolecular $O \rightarrow$ Si coordination in an *N*-[(chlorosilyl)methyl]amide system led to

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(2) (a) Obata, K.; Kabuto, C.; Kira, M. J. Am. Chem. Soc. 1997, 119, 11345–11346. (b) Yuan, C.-H.; West, R. Macromolecules 1994, 27, 629–630. (c) KariKari, E. K.; Greso, A. J.; Farmer, B. L.; Miller, R. D.; Rabolt, J. F. Macromolecules 1993, 26, 3937–3945. (d) Schilling, F. C.; Lovinger, A. J.; Davis, D. D.; Bovey, F. A.; Zeigler, J. M. Macromolecules 1993, 26, 2716–2723. (e) Harrah, L. A.; Zeigler, J. M. Macromolecules 1993, 26, 601–608. (f) Miller, R. D.; Hofer, D.; Rabolt, J. J. Am. Chem. Soc. 1985, 107, 2172–2174. (g) Miller, R. D.; Michl, J. Chem. Rev. 1989, 89, 1359–1410 and references therein.

(3) a) Imhof, R.; Teramae, H.; Michl, J. *Chem. Phys. Lett.* **1997**, *270*, 500–505. (b) Klingensmith, K. A.; Downing, J. W.; Miller, R. D.; Michl, J. J. Am. Chem. Soc. **1986**, *108*, 7438–7439.

(4) The term "*all-transoid*" denotes a backbone conformation whose dihedral angle is close to 165°. In the recent past, this conformation has been confused with "*all-trans* conformation"; however, "*all-trans*" should refer to a dihedral angle of 180°.

(5) Neumann, F.; Teramae, H.; Downing, J. W.; Michl, J. J. Am. Chem.
Soc. 1998, 120, 573-582.

(6) Recently, we have reported that introduction of pentacoordinate silicon atoms into oligosilanes leads to a drastic change in the electron transition energies of the Si–Si bonds: (a) El-Sayed, I.; Hatanaka, Y.; Muguruma, C.; Shimada, S.; Tanaka, M.; Koga, N.; Mikami, M. J. Am. Chem. Soc. **1999**, *121*, 5095–5096. (b) Muguruma, C.; Koga, N.; Hatanaka, Y.; El-Sayed, I.; Mikami, M.; Tanaka, M. J. Phys. Chem. A **2000**, *104*, 4928–4935.



Figure 1. X-ray structure of **1**. All hydrogen atoms and crystalline solvent are omitted for clarity. Selected bond distances (Å), bond angles (deg), and dihedral angle (deg): Si1–Si2 2.3480(9), Si2–Si3 2.3353(8), Si2–O1 1.990(2), Si2–Cl1 2.3499(7); C4–Si2–Cl1 88.22(7), Si1–Si2–Cl1 97.24(3), Si3–Si2–Cl1 90.96(3), Si1–Si2–C4 122.06(7), Si1–Si2–Si3 113.50(3), Si3–Si2–C4 124.08(7), O1–Si2–Cl1 170.70(5), Si2–Si3–Si2* 111.66(4); Si1–Si2–Si3–Si2* 163.61(3).



Figure 2. UV spectra of (a) a thin film of **1**, (b) **1** in ether solution, (c) a thin film of **2**, and (d) **1** in acetonitrile solution.

the almost undistorted trigonal bipyramidal (TBP) structure of **1** as indicated by the high %TBP_a and %TBP_e values for the pentacoordinate silicon atoms (89 and 99%, respectively).⁷ The most remarkable feature of the crystal structure of **1** is the *all-transoid* conformation of the silicon backbone. Thus, pentacoordinate pentasilane **1** has a stretched silicon chain; the Si–Si bond lengths (2.3353(8), 2.3480(9) Å), Si–Si–Si bond angles (113.50(3), 111.66(4)°), and Si–Si–Si–Si dihedral angle (163.61-(3)°) meet expectations for the *all-transoid* conformation.

The solid-state UV spectrum of the thin film of **1** exhibited an intense absorption at 257 nm, which is attributed to the $\sigma_{SiSi} \rightarrow \sigma^*_{SiSi}$ excitation of the silicon backbone with the *all-transoid* conformation (Figure 2a).^{6b} A weak absorption around 220 nm is assignable to the amide chromophore. To our surprise, the UV spectrum of **1** in ether solution was essentially similar to the solid-state spectrum, showing an intense absorption at 257 nm ($\epsilon = 22\ 000\ M^{-1}\ cm^{-1}$) (Figure 2b). The obvious similarity between the solid state and the solution spectra reveals that the most stable conformation of **1** is *all-transoid* even in a room-temperature solution, because UV spectra of oligosilanes are highly sensitive to the conformational change of the silicon backbones.^{3a} In sharp contrast, the conformational properties of tetracoordinate oligosi-

^{(7) %}TBP values indicate the degree of pentacoordinate character of a silicon atom: Tamao, K.; Hayashi, T.; Ito, Y.; Shiro, M. *Organometallics* **1992**, *11*, 2099–2114.

lanes are strikingly different from those of 1. For instance, the UV spectrum of the thin film of analogous tetracoordinate pentasilane Me₃SiSi(Cl)MeSiMe₂Si(Cl)MeSiMe₃ 2 (viscous liquid) showed three absorption maxima at 215, 230, and 255 nm, indicating that 2 exists as a mixture of several conformers in liquid state (Figure 2c).⁸ These results imply that the pentacoordinate silicon atoms effectively hinder the segmental motion of the silicon chains, stabilizing the all-transoid conformation.

²⁹Si NOE (nuclear Overhauser effect) experiments in deuterated benzene solution have provided conclusive evidence for the conformational rigidity of 1 in room-temperature solution. The negative NOE η values of ²⁹Si nucleus are correlated to the segmental motion of the silicon chains in solution.⁹ The $-\eta$ value of the central Si3 atom of 1 (-24.89 ppm) comes close to the limit, that is, 2.37 (94% DD relaxation),10 indicating that the segmental motion of the Si2-Si3-Si2* skeleton is nearly completely hindered. Thus, it is clear that the rotation about the Si2-Si3 bonds is completely inhibited in NMR time scale in ether and benzene solutions. In contrast, ²⁹Si NOE experiment in CD₃-CN revealed a marked decrease in the $-\eta$ value of the central Si3 atom (-11.75 ppm; $-\eta = 1.86$; 74% DD relaxation), indicating that the rotation about the Si2-Si3 bond is allowed in polar solvent. Consequently, the UV spectrum of 1 in acetonitrile solution displayed a broadening of the band with a significant decrease of the intensity ($\lambda_{max} = 253 \text{ nm}, \epsilon = 7500 \text{ M}^{-1} \text{ cm}^{-1}$) (Figure 2d), apparently due to the conformational lability of 1 in acetonitrile.

The origin of the conformational locking by the pentacoordinate silicon atoms is profoundly interesting. The relatively short Si2-Si3 bond length of 1 (2.3353(8) Å), which is comparable to that of Me₃Si-SiMe₃ (2.340(9) Å),¹¹ suggests that there is no appreciable steric interaction between the Si2 and Si3 atoms. Therefore, the conformational rigidity of 1 cannot be explained by the steric interference alone. To gain an insight into the nature of the rotational barriers about the Si2-Si3 bonds, the potential energy profile for the rotation was calculated by freezing the $Si1^*-Si2^*-Si3-Si2$ dihedral angle (ω) at 160° and optimizing all other coordinates (Figure 3).¹² The energy curves calculated by semiempirical PM3 method¹³ are essentially consistent with the experimental observations: for example, the presence of the all-transoid minimum at 200° [160° as w(Si1-Si2-Si3-Si2*)] and two energy maxima at 100° and 340°, which are 14.9 and 16.8 kcal/mol higher in energy than the *all-transoid* minimum, respectively.

In Figure 3, the calculated dipole moments of pentasilane 1 as a function of the dihedral angle ω are also shown. It is obvious that the change of the dipole moments of **1** is closely similar to that of the potential energy curve. Moreover, the hypervalent Cl-Si-O bonds should have a large dipole moment as a result of donor-acceptor $O \rightarrow Si$ interaction involving charge transfer.¹⁴



Figure 3. (a) Potential energy of **1** as a function of the dihedral angle ω (Si1-Si2-Si3-Si2*). For the rotation around the Si2-Si3 bond, change of the ω is positive for counterclockwise rotation when viewed from the side of the Si1 atom. (b) Change of dipole moment of 1 as a function of the ω (Si1-Si2-Si3-Si2*).

All of these things make it clear that electrostatic interactions between the strongly polarized Cl-Si-O bonds play a critical role in hindering the rotation about the Si2-Si3 bonds. Thus, the *all-transoid* conformer is effectively stabilized by cancellation of the bond dipole moments, whereas other conformers would be significantly destabilized by unfavorable alignment of the bond dipoles.¹⁵ The conformational lability of **1** in highly polar solvents such as acetonitrile is entirely consistent with this conclusion.¹⁶

These results can be sharply contrasted with the situation in tetracoordinate peralkylated silicon chains, where the contribution of electrostatic interactions to the rotational barriers are negligible.⁵ Thus, it is concluded that retardation of the free rotation about Si-Si bonds by pentacoordinate silicon atoms is a unique and most practical method for locking the conformations of silicon chains. Although conformational control of oligosilanes by steric interactions between the substituents¹⁷ or conformationally rigid cyclic systems^{8a,18} have been recently reported, this is the first example where hypervalent silicon atoms exert a strong influence on the backbone conformation. This strategy will stimulate the development of useful organic materials with unique electronic and optical properties which cannot be realized by tetracoordinate silicon compounds.19

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Supporting Information Available: Experimental details and characterization data for all new compounds, including the results of NOE experiments and X-ray experimental details (PDF). This material is available free of charge via the Internet at http://pubs.acs.org.

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⁽⁸⁾ Silicon chains adopting all-transoid conformation usually exhibit a single absorption band: (a) Mazieres, S.; Raymond, M. K.; Raabé, G.; Prodi, A.; Michl, J. J. Am. Chem. Soc. **1997**, 119, 6682-6683. (b) Plitt, H. S.; Balaji, (9) The silicon atoms with limited mobility relax predominantly via the

dipole-dipole mechanism as shown by the large $-\eta$ values (DD relaxation), while more mobile silicon atoms tend to relax via a spin-rotation mechanism as indicated by smaller $-\eta$ values (SR relaxation): (a) Levy, G. C.; Cargioli, J. D.; Juliano, P. C.; Mitchell, T. D. J. Am. Chem. Soc. **1973**, 95, 3445– 3454. (b) Pannell, K. H.; Bassindale, A. R. J. Organomet. Chem. 1982, 229, 1 - 9

⁽¹⁰⁾ NOE η value of -2.52 corresponds to 100% DD relaxation. The contribution of DD relaxation mechanism to spin–lattice (T_1) ralaxation is indicated by % DD relaxation value defined as $-\eta/2.52 \times 100.\%$ (11) Beagley, B.; Monaghan, J. J.; Hewitt, T. G. J. Mol. Struct. **1971**, 8,

^{401 - 411}.

⁽¹²⁾ Although this method does not yield all conformational minima of 1, it is sufficient for quantitative understanding of the nature of the rotational barriers

⁽¹³⁾ Stewart, J. J. P. J. Comput. Chem. 1989, 10, 221-264.

⁽¹⁵⁾ The PM3 calculations indicate the charge distributions for Cl (-0.665), Si2 (0.549), and O (-0.310) atoms

⁽¹⁶⁾ Wong, M. W.; Frisch, M. J.; Wiberg, K. B. J. Am. Chem. Soc. 1991, 113, 4776-4782

⁽¹⁷⁾ Tanaka, R.; Unno, M.; Matsumoto, H. Chem. Lett. 1999, 595-596. (18) Tamao, K.; Tsuji, H.; Terada, M.; Asahara, M.; Yamaguchi, S.; Toshimitsu, A. Angew. Chem., Int. Ed. 2000, 39, 3287-3290.

⁽¹⁹⁾ For example, the emission property of 1 is vastly different from those of tetracoordinate oligosilanes. Thus, 1 exhibited fluorescence emission at 283.4 nm when excited at 260.0 nm is souchae at room temperature. The observed Stokes shift (3175 cm⁻¹) is markedly small, compared to that of tetracoordinate oligosilanes such as $Me_{12}Si_5$ which shows the emission at 370 nm with a large Stokes shift (13 000 cm $^{-1}).^{8b}$